

Product Data Sheet



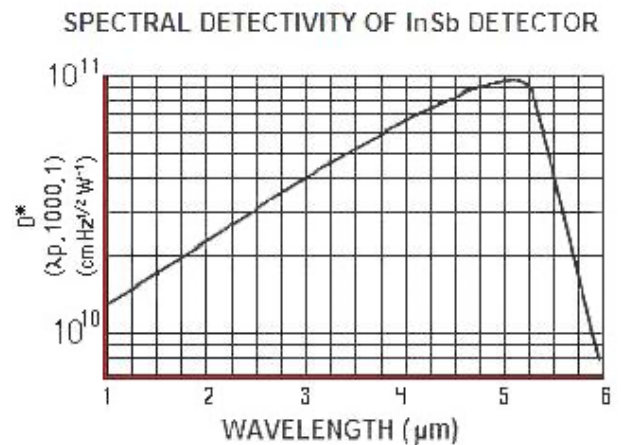
The photovoltaic **Indium Antimonide** detectors offered by **InfraRed Associates, Inc.** are p-n junctions formed by mesa techniques using single crystal material. This process yields the highest quality photodiodes which exhibit excellent electro-optical performance in the 1 μ m to 5.5 μ m wavelength region. These diodes are background limited (BLIP) detectors and their performance can be enhanced by spatial (cooled FOV stops) or spectral (cooled interference filters) reduction of the background.

Typical Application:

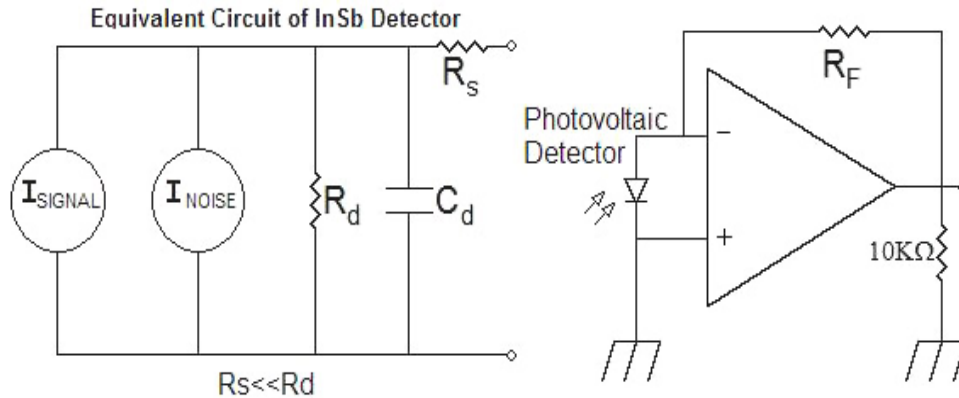
- Medical Thermography
- Thermal Imaging
- Spectroscopy
- Radiometry
- Research
- IR Microscopy

The photovoltaic effect is the generation of a potential across the p-n junction when radiation of the proper wavelength is incident upon it. When the photon flux irradiates the junction, electron-hole pairs are formed if the photon energy exceeds the forbidden gap energy.

The field sweeps the electrons from the p region to the n region, and holes from the n region to the p region. This process makes the p region positive and the n region negative, and will produce current flow in an external circuit. An equivalent circuit of the InSb detector is represented below. This consists of both a signal and noise current generator in parallel with a resistive and capacitive term.



InSb Detectors



When background radiation shifts the operation curve by generating a constant output in the active element, the detector should be reversed-biased to bring it back to the optimum operating point: zero voltage.

This can be achieved by utilizing a matched preamplifier such as our IAP-1000IS . The detector preamplifier system operates in the detector noise limited mode. A dual output supply is required.

Standard Photovoltaic Indium Antimonide Detectors

Model Number	FOV=60°, (λpk,1000,1)								Std. Pkg.	Std. Window	
	Active Area Element (mm)	D* (cmHz ^{1/2} W ⁻¹)	Responsivity (λp)	Resistance (Rd) (Ω)	Capacitance (Cd) (pF)	Short Circuit Current Isc (μA)	Open Circuit Voltage Vcc (mV)	Operating Temp. (K)			
IS-1.0	1/1x1	≥ 1.0E11	≥ 3 A/W	350K	350	8	80 to 125	77	MSL-8 MSL-12 or MDL-8 MDL-12	Sapphire	
IS-2.0	2/2x2			100K	1500	30					
MSL-8 Side Looking Metal Dewar---8 Hour Hold Time					MSL-12 Side Looking Metal Dewar---12 Hour Hold Time						
MDL-8 Down Looking Metal Dewar---8 Hour Hold Time					MDL-12 Down Looking Metal Dewar---12 Hour Hold Time						

Contact Details

Manufacturer

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Disclaimer

This data sheet has been compiled to the best of our knowledge and with the utmost care. Nevertheless, we cannot guarantee that the information contained herein is up to date, accurate, complete or suitable for specific applications. The technical data and specifications are provided solely for the purpose of providing non-binding preliminary information. They do not constitute any warranted characteristics in the legal sense.

The user is obliged to check the suitability and applicability of the product for their specific intended use on their own responsibility. We accept no liability for any damage arising from the use of the information provided here.

We expressly reserve the right to make changes to the technical data and to correct any errors.